

Features

- Uses advanced SGT technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)

Application

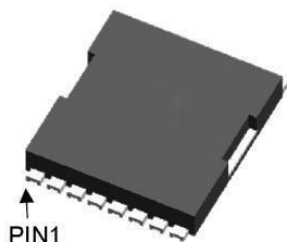
- Motor control and drive
- Battery management
- UPS

Product Summary

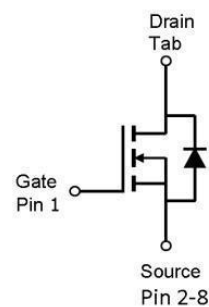
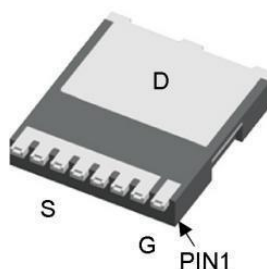
Package	TOLL
V_{DS}	200V
$R_{DS(on)}$ @ $V_{GS}=10V$	6.5mΩ
I_D	160A

Package Marking

TOLL Top View



TOLL Bottom View



Type	Package	Marking	Reel Size	Tape Width	Packing	Qty
LR075N20SW10	TOLL	LR075N20SW10	330*28.5mm	24mm	Reel&Tape	2000

Maximum Ratings (TC=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous drain current $T_c=25^{\circ}C$ (Silicon limit) $T_c=100^{\circ}C$ (Silicon limit)	I_D	160 100	A
Pulsed Drain Current	I_{DM}	640	A
Maximum Power Dissipation	P_d	357	W
Single pulse avalanche energy	E_{AS}	1106	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance,Junction-to-Case	R_{thJC}	0.35	°C/W
Thermal Resistance,Junction-to-Ambient	R_{thJA}	62	

Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	min	typ	max	Unit
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Static Characteristic

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	200	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.3	3.3	4.3	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=200V, V_{GS}=0V$	-	-	1	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D=40A, V_{GS}=10V$	-	6.5	7.5	mΩ
Transconductance	g_{FS}	$V_{DS}=5V, I_D=60A$	-	210	-	S

Dynamic Characteristic

Input Capacitance	C_{iss}	$V_{DS}=100V, V_{GS}=0V,$ $f=1MHz$	-	11500	-	pF
Output Capacitance	C_{oss}		-	490	-	
Reverse Transfer Capacitance	C_{rss}		-	23	-	
Gate resistance	R_g	$f=1MHz$	-	1.9	-	Ω
Gate Total Charge	Q_g	$V_{DS}=100V, I_D=50A,$ $V_{GS}=10V$	-	175	-	nC
Gate-Source charge	Q_{gs}		-	65	-	
Gate-Drain charge	Q_{gd}		-	35	-	
Turn-on delay time	$t_{d(on)}$	$V_{GS}=10V, V_{DS}=100V,$ $R_G=3\Omega$	-	40	-	ns
Rise time	t_r		-	63	-	
Turn-off delay time	$t_{d(off)}$		-	105	-	
Fall time	t_f		-	30	-	

Body Diode Characteristic

Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=100A$	-	-	1.4	v
Reverse Recovery Time	t_{rr}	$I_F = 100A$ $di/dt = 100A/\mu s$	-	140	-	ns
Reverse Recovery Charge	Q_{rr}		-	815	-	nC

Typical Performance Characteristics

Fig 1: Output Characteristics

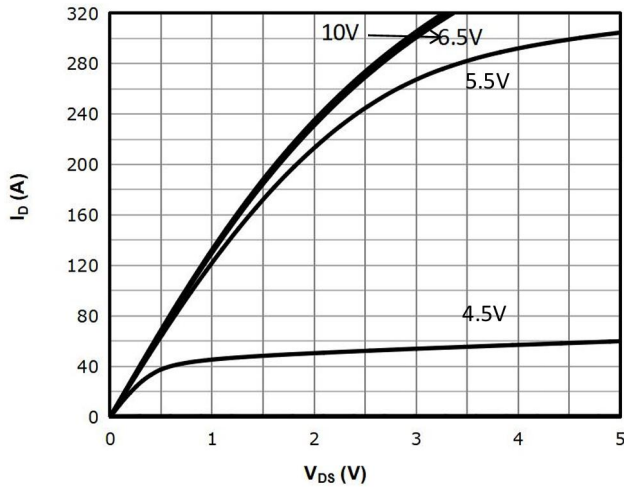


Fig 2: Transfer Characteristics

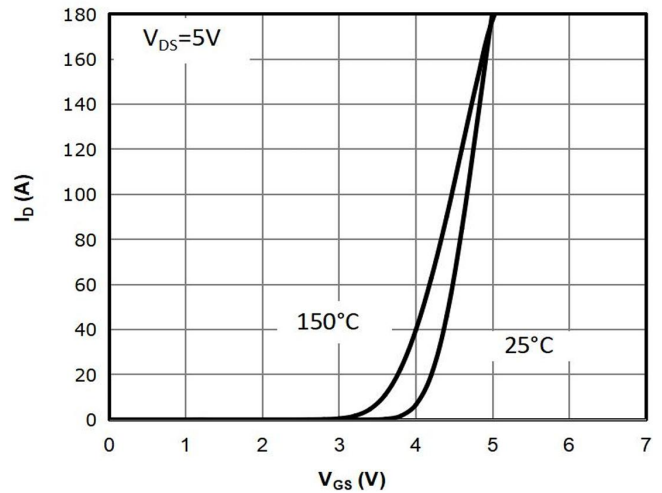


Fig 3: Rds(on) vs Drain Current

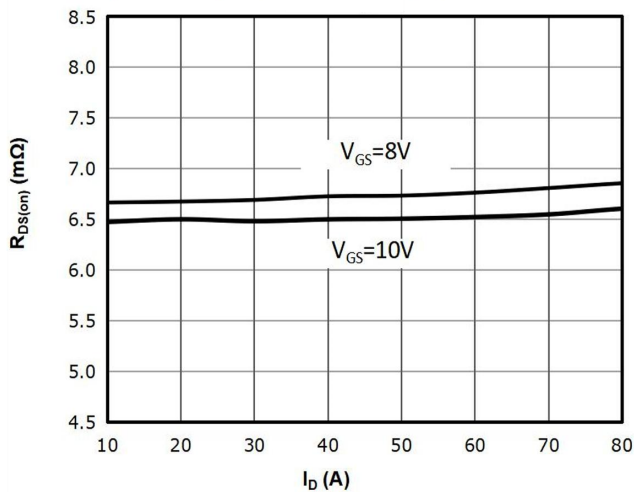


Fig 4: Rds(on) vs Gate Voltage

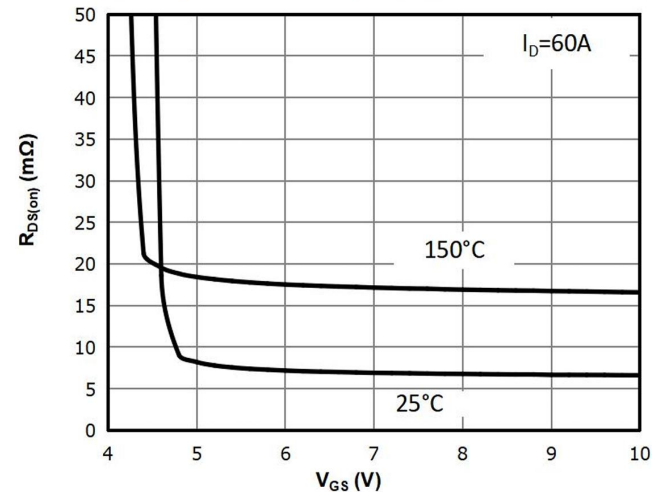


Fig 5: Rds(on) vs. Temperature

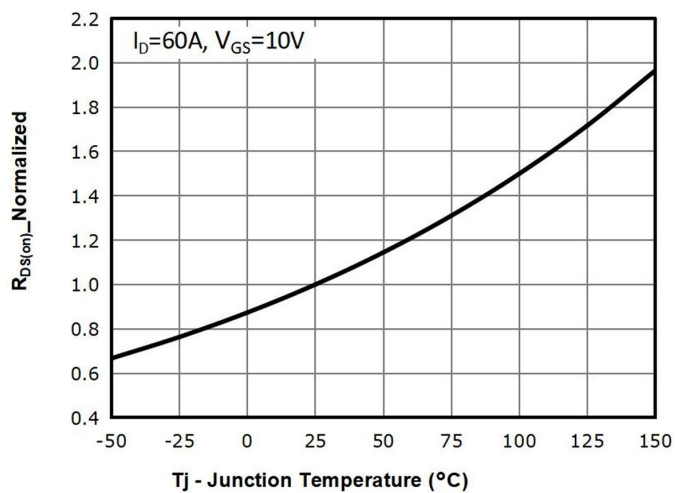


Fig 6: Vgs(th) vs. Temperature

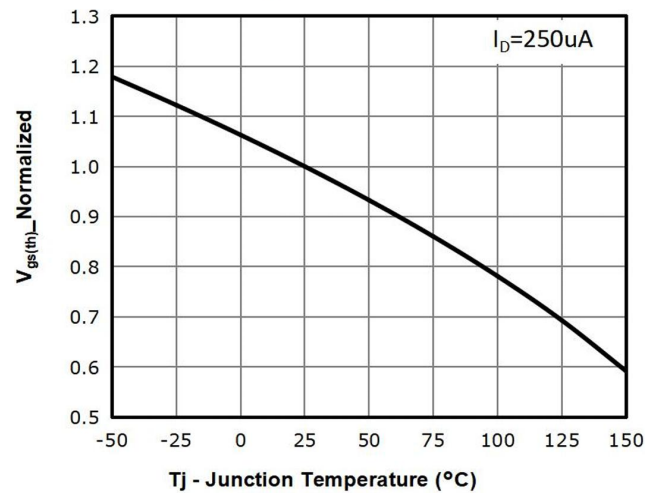


Fig 7: BVdss vs. Temperature

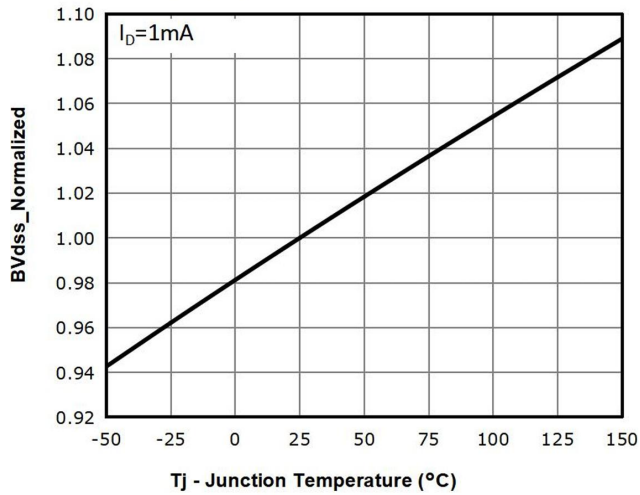


Fig 8: Capacitance Characteristics

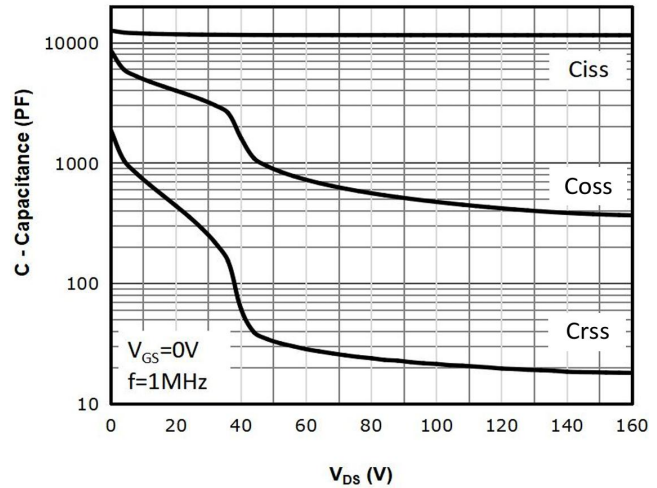


Fig 9: Gate Charge Characteristics

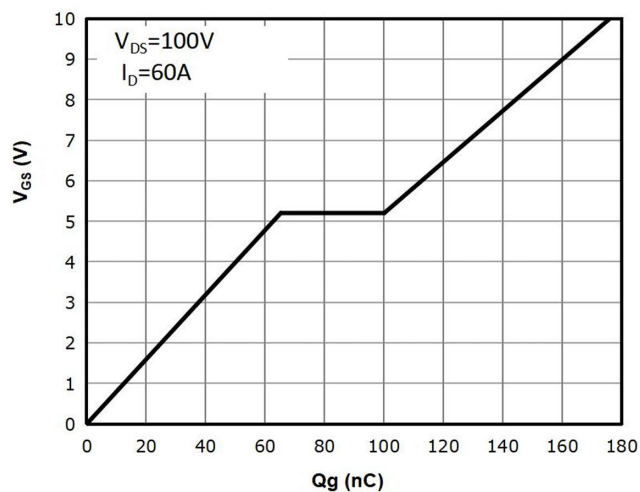


Fig 10: Body-diode Forward Characteristics

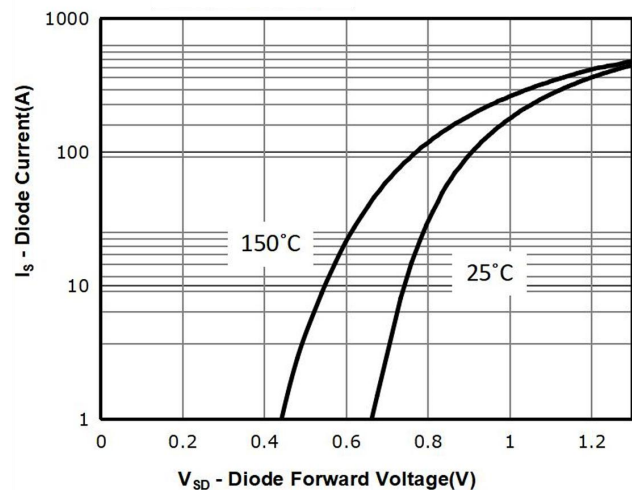


Fig 11: Power Dissipation

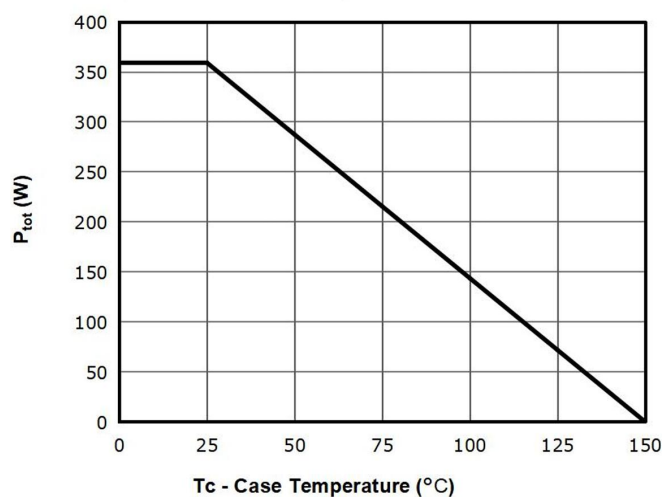


Fig 12: Drain Current Derating

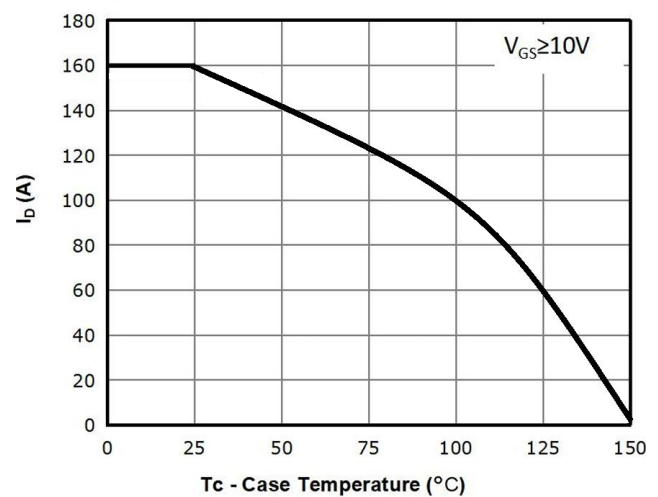


Fig 13: Safe Operating Area

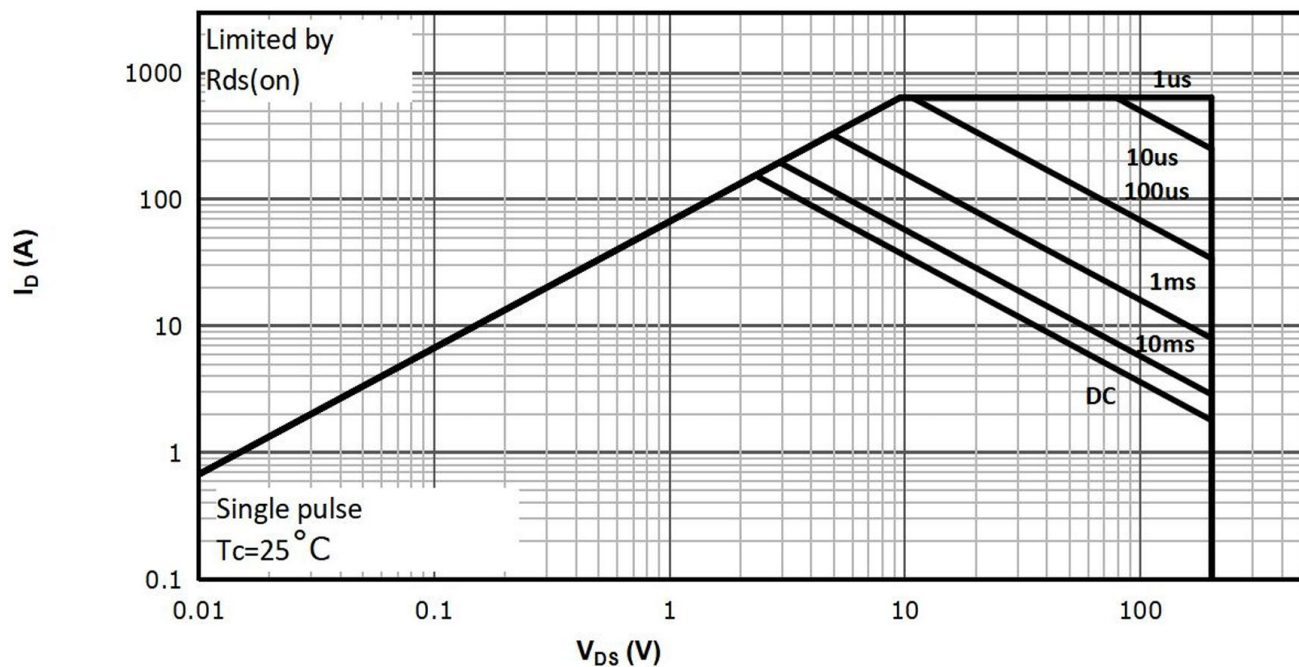
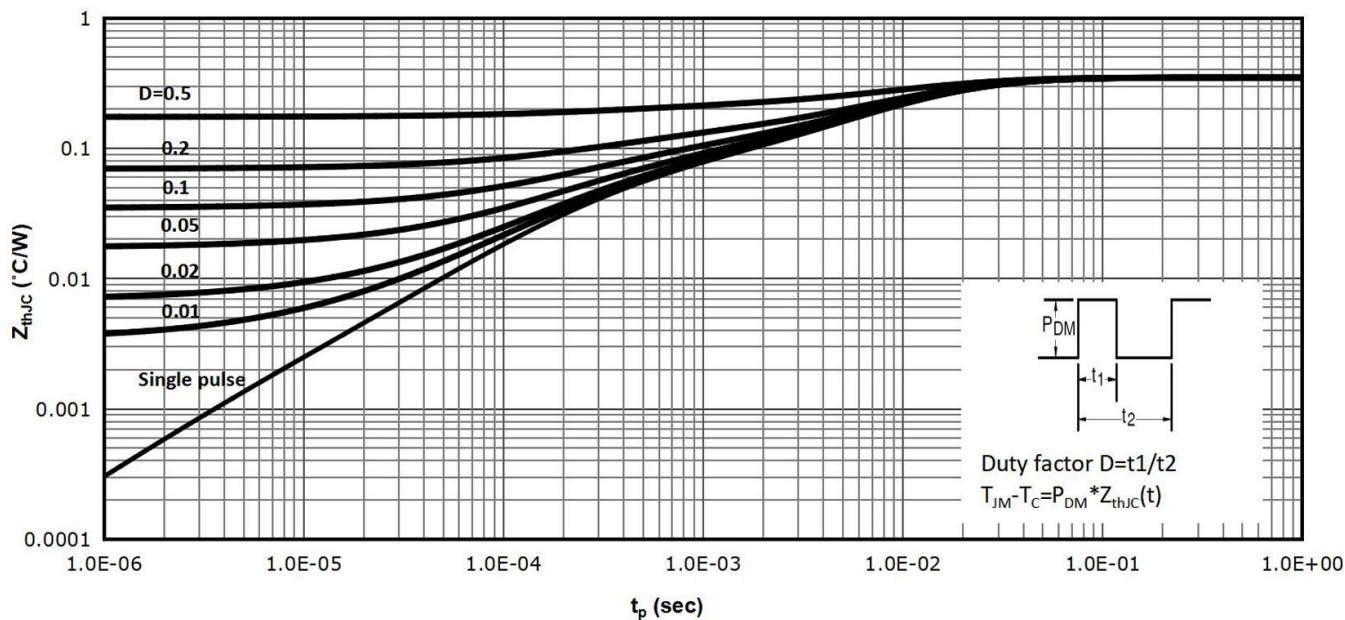
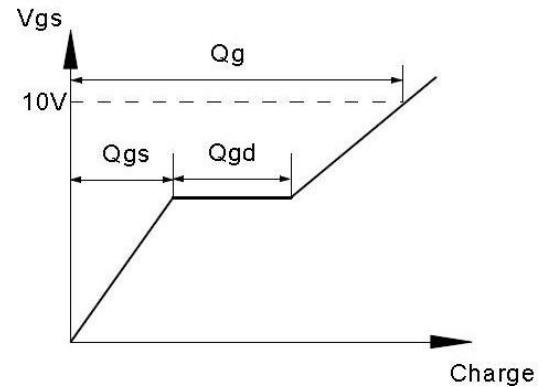
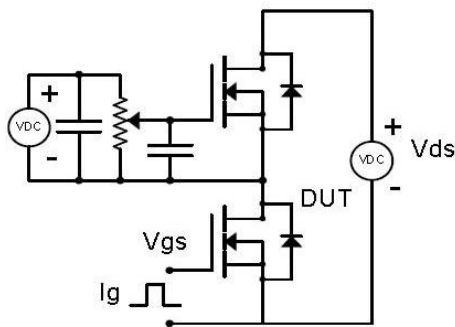


Fig 14: Max. Transient Thermal Impedance

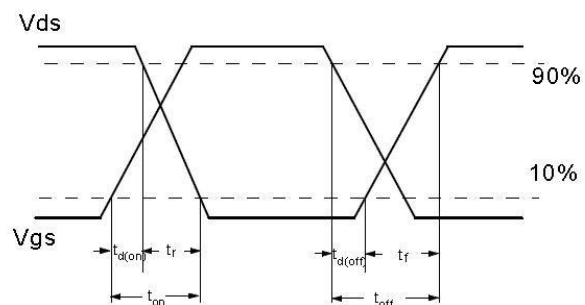
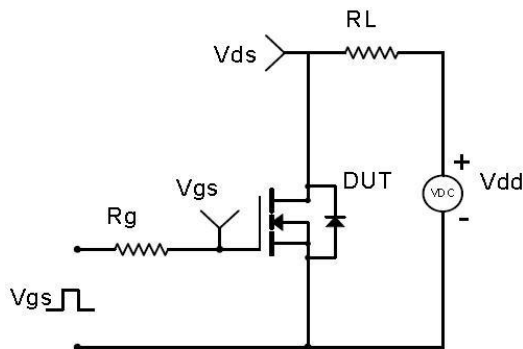


Test Circuit & Waveform

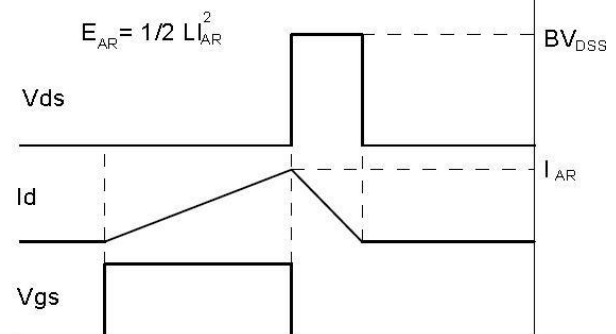
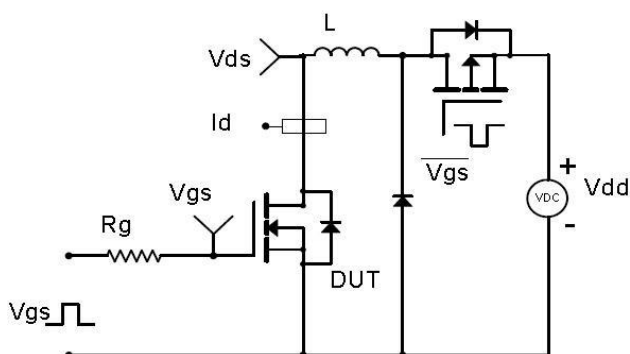
Gate Charge Test Circuit & Waveform



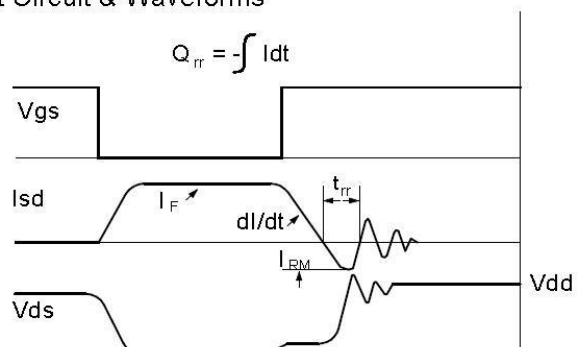
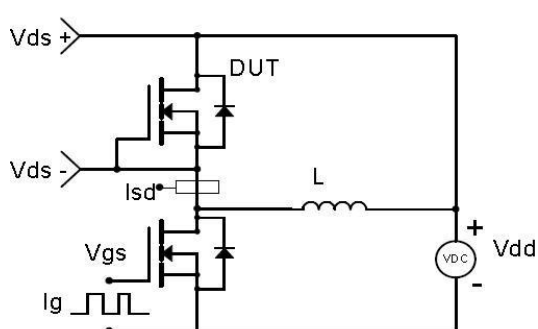
Resistive Switching Test Circuit & Waveforms



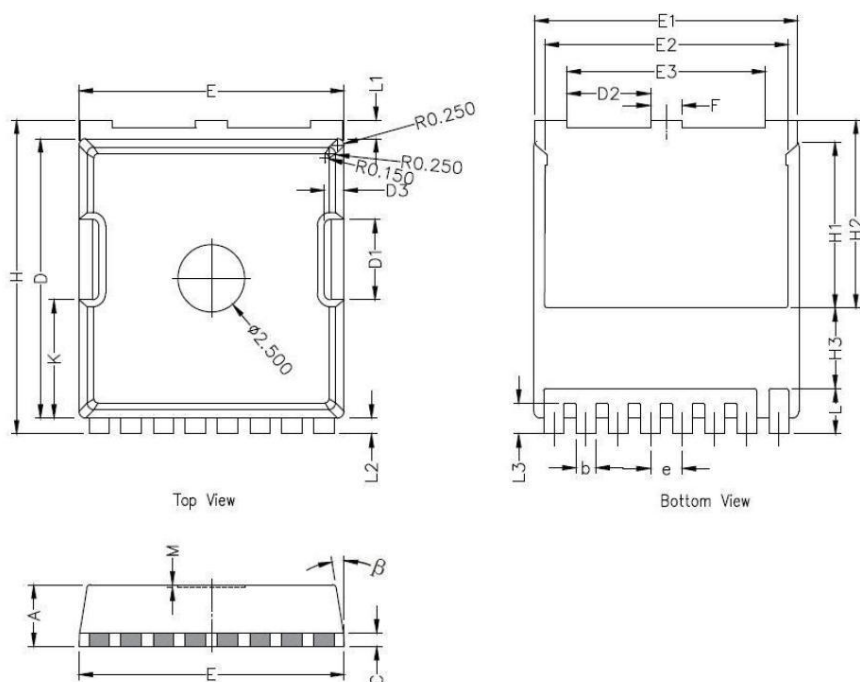
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline:TOLL



Symbols	Millimeters		
	MIN.	NOM	MAX.
A	2.20	2.30	2.40
b	0.65	0.75	0.85
C	0.508 REF		
D	10.25	10.40	10.55
D1	2.85	3.00	3.15
D2	2.95	3.10	3.25
D3	0.75 REF		
E	9.75	9.90	10.05
E1	9.65	9.80	9.95
E2	8.95	9.10	9.25
E3	7.25	7.40	7.55
e	1.20 BSC		
F	1.05	1.20	1.35
H	11.55	11.70	11.85
H1	6.03	6.18	6.33
H2	6.85	7.00	7.15
H3	3.00 BSC		
L	1.55	1.70	1.85
L1	0.55	0.70	0.85
L2	0.45	0.60	0.75
L3	1.00	1.15	1.30
M	0.08 REF		
β	8°	10°	12°
K	4.25	4.40	4.55

Revision History:

Revision	Date	Major changes
1.0	2026/1/10	Release of Preliminary version.